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Claim 19. (Currently Amended) A pair of lead frames for use in a light-emitting apparatus of a flip chip bonding type, said apparatus comprising:

a transparent base having a first surface;
first and a second bonding pads formed on said first surface; and
a GaN semiconductor light-emitting device fixed on the first surface,

wherein a first lead frame includes a first mount which faces a dominant light emitting direction of the light-emitting apparatus and on which the first bonding pad is to be fixed, and a second lead frame includes a second mount which faces the dominant light emitting direction and on which the second bonding pad is to be fixed,

wherein the light-emitting device comprises a substrate, a light-emitting layer and a positive electrode comprising a light non-transmissible material, said positive electrode being disposed on an opposite side of said light-emitting layer from said substrate and reflecting light from said light-emitting layer in a direction through said substrate and said base,

wherein said positive electrode is connected by a bonding wire to a same surface of one of said first and second bonding pads as one of said pair of lead frames.

Claim 20. (Original) A pair of lead frames according to claim 19, wherein the first lead frame has a first projection on which diffused light from the light-emitting device is to be reflected toward the dominant light-emitting direction, and the second lead frame has a second projection on which diffused light from the light-emitting device is to be reflected toward the dominant light-emitting direction.

Claim 21. (Currently Amended) A light-emitting diode comprising:

a sapphire substrate;
a light-emitting light-emitting layer comprising made of GaN semiconductor and formed on said sapphire substrate; and
a positive electrode and a negative electrode electrically coupled to said light-emitting layer;

wherein said positive electrode and said negative electrode are supplied with electricity through a wire₁; and

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wherein said positive electrode has a thickness of at least 5000Å ~~300Å~~, comprises a light non-transmissible material for reflecting light from said light emitting layer toward said sapphire substrate, and covers substantially an entire surface of the light-emitting layer.

Claim 22. (Previously Added) A semiconductor light-emitting apparatus of flip chip bonding type as claimed in claim 14, wherein the light-emitting layer comprises a multi-quantum well layer.

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Claim 23. (Previously Added) A pair of lead frames for use in a light-emitting apparatus of flip chip bonding type as claimed in claim 19, wherein the light-emitting layer comprises a multi-quantum well layer.

Claim 24. (Previously Added) A light-emitting diode as claimed in claim 21, wherein the light-emitting layer comprises a multi-quantum well layer.

Claim 25. (Currently Amended) A light-emitting diode as claimed in claim 21, further comprising:

a layer containing a fluorescent material formed on a side of the sapphire substrate.

Claim 26. (Currently amended) A semiconductor light-emitting apparatus comprising:

a base;

first and second bonding pads formed on a first surface of said base;

a light-emitting element formed between said first and second pads on said first surface of said base; said light-emitting element comprising:

a substrate;

a light-emitting layer formed on said substrate; and

a first electrode disposed on an opposite side of said light-emitting layer from said base and comprising a light non-transmissible material for reflecting light from said light-emitting layer through said base; and

a fluorescent material which is adjacent to said substrate and on an opposite side of said substrate from said light-emitting layer.

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Claim 27. (Previously Added) The semiconductor light-emitting apparatus according to claim 26, further comprising:

first and second lead frames electrically connected to said first and second bonding pads, respectively.

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Claim 28. (Previously Added) The semiconductor light-emitting apparatus according to claim 27, wherein said light-emitting element further comprises a substrate disposed between said light-emitting layer and said base, and wherein said first electrode reflects light from said light-emitting layer through said substrate.

Claim 29. (Previously Added) The semiconductor light-emitting apparatus according to claim 27, wherein a direction from said light-emitting layer toward said base comprises a dominant light-emitting direction.

Claim 30. (Previously Added) The semiconductor light-emitting apparatus according to claim 29, wherein said first and second lead frames each comprise a projecting portion which reflects light in said dominant light-emitting direction.

Claim 31. (Previously Added) The semiconductor light-emitting apparatus according to claim 27, wherein said first and second bonding pads are formed on said first surface of said base so as to maximize a distance between said first and second lead frames.

Claim 32. (Previously Added) The semiconductor light-emitting apparatus according to claim 26, wherein first and second bonding pads are formed on opposing outer edges of said first surface of said base.

Claim 33. (Previously Added) The semiconductor light-emitting apparatus according to claim 26, wherein an adhesive adheres said light-emitting element to said first surface of said base.

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Claim 34. (Previously Added) The semiconductor light-emitting apparatus according to claim 26, wherein said light-emitting element further comprises a second electrode, said first and second electrodes being connected by bonding wires to said first and second bonding pads, respectively.

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Claim 35. (Previously Added) The semiconductor light-emitting apparatus according to claim 34, wherein said first and second lead frames and said bonding wires are connected to a same surface of said first and second bonding pads.

Claim 36. (Previously Added) The semiconductor light-emitting apparatus according to claim 28, wherein said substrate of said light-emitting element is formed on said base.

Claim 37. (Previously Added) The semiconductor light-emitting apparatus according to claim 14, further comprising:

a fluorescent material which is adjacent to said substrate and on an opposite side of said substrate from said light-emitting layer.

Claim 38. (Previously Added) The pair of lead frames according to claim 19, wherein said apparatus further comprises a sealing resin formed over said transparent base and said GaN semiconductor light-emitting device.
